PROCESS CPZ19

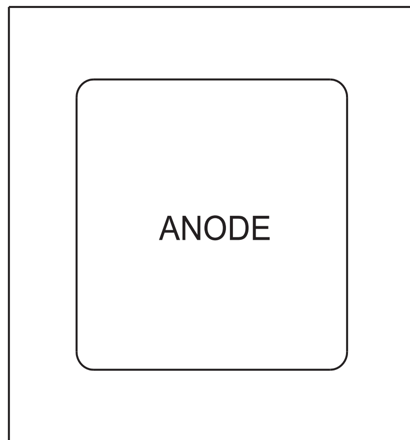
Zener Diode

0.5 Watt Zener Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	17.7 x 17.7 MILS
Die Thickness	7.5 MILS
Anode Bonding Pad Area	11 x 11 MILS
Top Side Metalization	Al - 13,000Å
Back Side Metalization	Au - 14,000Å

GEOMETRY



BACKSIDE CATHODE R0

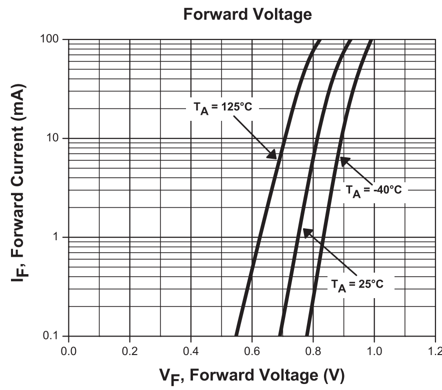
GROSS DIE PER 4 INCH WAFER
36,642

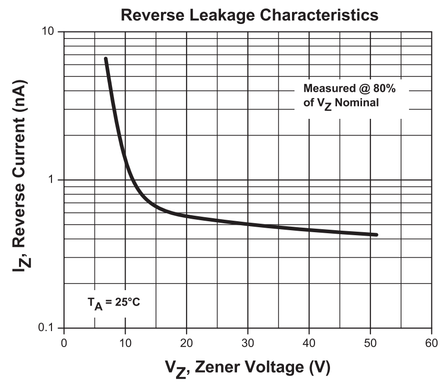
PRINCIPAL DEVICE TYPES
CMPZ5235B
THRU
CMPZ5261B

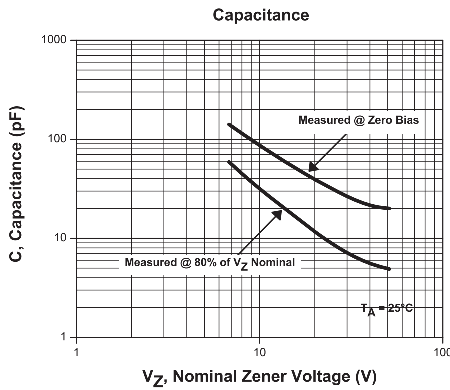
R5 (22-March 2010)

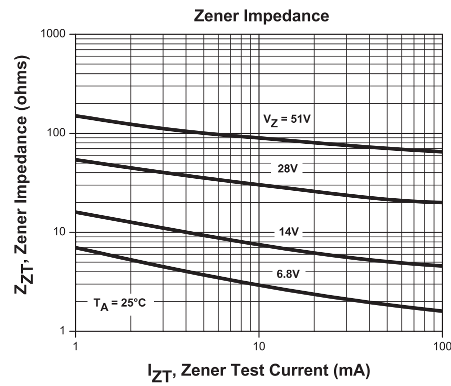
PROCESS CPZ19

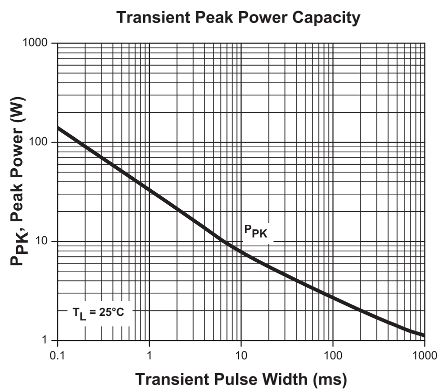
Typical Electrical Characteristics

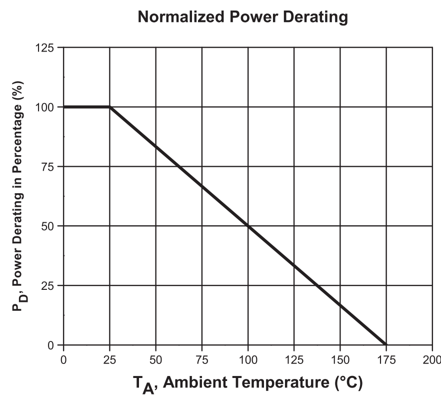












R5 (22-March 2010)